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Automotive High Performance Logic Gates

NLV18SGxx, NLV28WGxx

The NLV18SGxx are automotive-grade High Performance single CMOS logic gates. The NLV28WGxx are automotive-grade high Performance Dual CMOS logic gates.

Features

- High Speed: $t_{PD} = 3.7$ ns (Typ) at $V_{CC} = 3.0$ V, $C_L = 15$ pF
- Low Power Dissipation: $I_{CC} = 0.5$ μ A (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity
- Balanced Propagation Delays ($t_{PLH} = t_{PHL}$)
- 3.6 V Overvoltage-Tolerant Input and Output Pins
- AEC Grade 1-Compliant: -40°C to $+125^\circ\text{C}$
- Tiny SC-88A and SC-88 Packages
- AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and RoHS Compliant

FUNCTION LIST

xx	Function
00	2-Input NAND
02	2-Input NOR
04	Inverter
06	Open-Drain Inverter
07	Open-Drain Buffer
08	2-Input AND
14	Schmitt-Trigger Inverter
17	Schmitt-Trigger Buffer
32	2-Input OR
34	Buffer
86	2-Input XOR
125	Tri-State Buffer
126	Tri-State Buffer
U04	Unbuffered Inverter



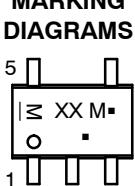
ON Semiconductor®

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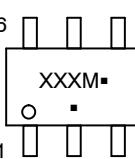
MARKING DIAGRAMS



SC-88A
DF SUFFIX
CASE 419A



SC-88
CASE 419B



XX = Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

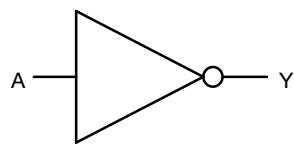
*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

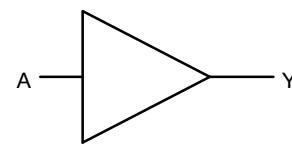
NLV18SGxx, NLV28WGxx

Functions and Function Tables – Buffers and Inverters



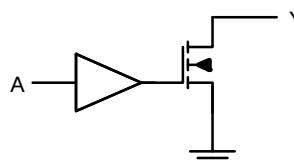
04 – Inverter
U04 – Unbuffered Inverter

A	Y
0	1
1	0



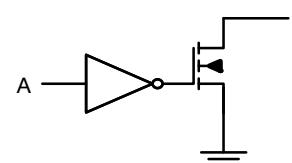
34 – Buffer

A	Y
0	0
1	1



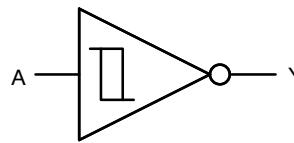
06 – Open-Drain Inverter

A	Y
0	Hi-Z
1	0



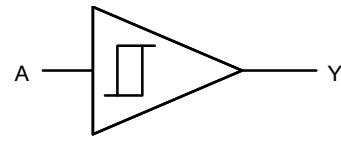
07 – Open-Drain Buffer

A	Y
0	0
1	Hi-Z



14 – Schmitt-Trigger Inverter

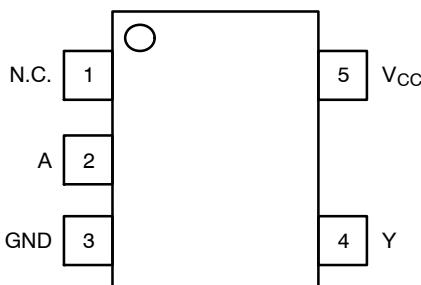
A	Y
0	1
1	0



17 – Schmitt-Trigger Buffer

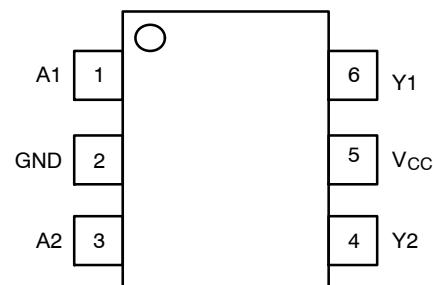
A	Y
0	0
1	1

Pin Assignment



Pinout (Single Buffers and Inverters)

Pin	Name	Description
1	N.C.	No Connection
2	A	Input
3	GND	Ground
4	Y	Output
5	V _{CC}	Supply

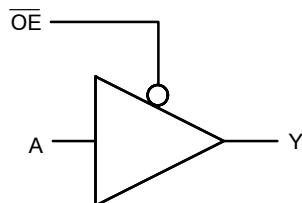


Pinout (Dual Buffers and Inverters)

Pin	Name	Description
1	A1	Input 1
2	GND	Ground
3	A2	Input 2
4	Y	Output 2
5	V _{CC}	Supply
6	Y1	Output 1

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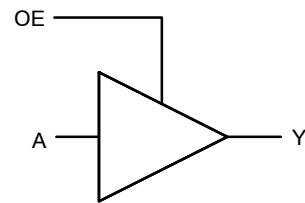
Functions and Function Tables – Tri-State Buffers and Bus Drivers



125 – Tri-State Buffer

OE	A	Y
0	0	0
0	1	1
1	X	Hi-Z

X = Don't Care

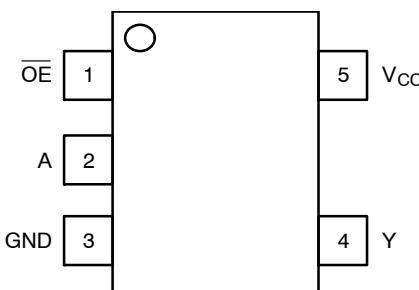


126 – Tri-State Buffer

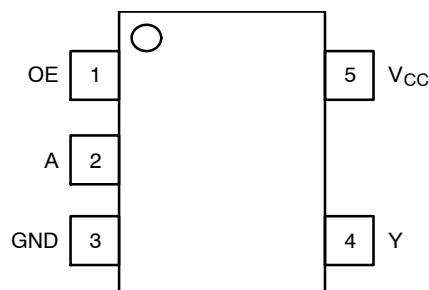
OE	A	Y
0	X	Hi-Z
1	0	0
1	1	1

X = Don't Care

Pin Assignments



Pinout (125)



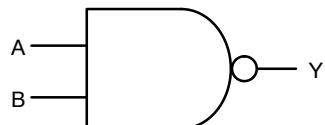
Pinout (126)

Pin	Name	Description
1	OE	Enable (Active-Low)
2	A	Input
3	GND	Ground
4	Y	Output
5	V _{CC}	Supply

Pin	Name	Description
1	OE	Enable (Active-High)
2	A	Input
3	GND	Ground
4	Y	Output
5	V _{CC}	Supply

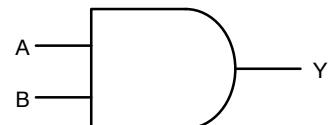
NLV18SGxx, NLV28WGxx

Functions and Function Tables – Gates



00 – NAND

A	B	Y
0	0	1
0	1	1
1	0	1
1	1	0



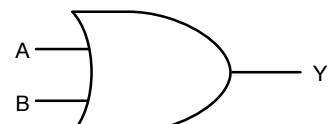
08 – AND

A	B	Y
0	0	0
0	1	0
1	0	0
1	1	1



02 – NOR

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	0



32 – OR

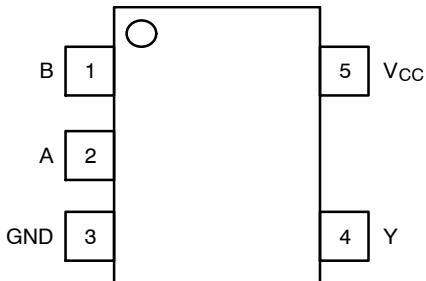
A	B	Y
0	0	0
0	1	1
1	0	1
1	1	1



86 – XOR

A	B	Y
0	0	0
0	1	1
1	0	1
1	1	0

Pin Assignment



Pinout (Gates)

Pin	Name	Description
1	B	Input
2	A	Input
3	GND	Ground
4	Y	Output
5	V _{CC}	Supply

NLV18SGxx, NLV28WGxx

Table 1. MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +4.3	V
V _{IN}	DC Input Voltage	-0.5 to +4.3	V
V _{OUT}	DC Output Voltage (U04)	-0.5 to V _{CC} +0.5	V
	DC Output Voltage (Other functions)	Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V _{CC} = 0 V)	
I _{IK}	DC Input Diode Current	-20	mA
I _{OK}	DC Output Diode Current	-20	mA
I _{OUT}	DC Output Source/Sink Current	±20	mA
I _{CC} or I _{GND}	DC Supply Current Per Supply Pin or Ground Pin	±20	mA
T _{TSG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature Under Bias	+150	°C
θ _{JA}	Thermal Resistance (Note 2)	377	°C/W
P _D	Power Dissipation in Still Air	332	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model	2000
		Charged Device Model	1000
I _{LATCHUP}	Latchup Performance (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri–stated.

2. Measured with minimum pad spacing on an FR4 board, using 10 mm–by–1 inch, 20 ounce copper trace with no air flow per JESD51–7.

3. HBM tested to EIA / JESD22–A114–A. CDM tested to JESD22–C101–A. JEDEC recommends that ESD qualification to EIA/JESD22–A115A (Machine Model) be discontinued.

4. Tested to EIA/JESD78 Class II.

Table 2. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	0.9	3.6	V
V _{IN}	Digital Input Voltage	0	3.6	V
V _{OUT}	DC Output Voltage (U04)	0	V _{CC}	V
	DC Output Voltage (Other functions)	0	V _{CC} 3.6 3.6	
T _A	Operating Free–Air Temperature	-40	+125	°C
	Input Transition Rise or Fall Rate			ns/V
		0	No Limit	
	All Other Functions	V _{CC} = 3.3 V ± 0.3 V	0	10

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

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Table 3. DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V _{CC} (V)	T _A = 25°C			T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	

FUNCTIONS 14 and 17

V _{T+}	Positive-Going Threshold		0.9	–	0.6	–	–	–	V
			1.1	–	0.73	0.95	–	0.95	
			1.4	–	0.92	1.16	–	1.16	
			1.65	–	1.07	1.3	–	1.3	
			2.3	–	1.44	1.73	–	1.73	
			3.0	–	1.82	2.24	–	2.24	
V _{T-}	Negative-Going Threshold		0.9	–	0.34	–	–	–	V
			1.1	0.15	0.4	–	0.15	–	
			1.4	0.3	0.52	–	0.3	–	
			1.65	0.35	0.62	–	0.35	–	
			2.3	0.55	0.92	–	0.55	–	
			3.0	0.95	1.24	–	0.95	–	
V _H	Hysteresis Voltage		0.9	–	0.27	–	–	–	V
			1.1	0.2	0.33	0.8	0.2	0.8	
			1.4	0.25	0.5	0.86	0.25	0.86	
			1.65	0.3	0.5	0.9	0.3	0.9	
			2.3	0.4	0.5	1.05	0.4	1.05	
			3.0	0.49	0.65	1.1	0.49	1.1	

FUNCTION U04 (Under Development)

V _{IH}	High-Level Input Voltage		0.9	–	TBD	–	–	–	V
			1.1 to 1.3	TBD	–	–	TBD	–	
			1.4 to 1.6	TBD	–	–	TBD	–	
			1.65 to 1.95	TBD	–	–	TBD	–	
			2.3 to 2.7	TBD	–	–	TBD	–	
			3.0 to 3.6	TBD	–	–	TBD	–	
V _{IL}	Low-Level Input Voltage		0.9	–	TBD	–	–	–	V
			1.1 to 1.3	–	–	TBD	–	TBD	
			1.4 to 1.6	–	–	TBD	–	TBD	
			1.65 to 1.95	–	–	TBD	–	TBD	
			2.3 to 2.7	–	–	TBD	–	TBD	

ALL OTHER FUNCTIONS

V _{IH}	High-Level Input Voltage		0.9	V _{CC}	–	–	V _{CC}	–	V
			1.1 to 1.3	0.7 × V _{CC}	–	–	0.7 × V _{CC}	–	
			1.4 to 1.6	0.65 × V _{CC}	–	–	0.65 × V _{CC}	–	
			1.65 to 1.95	0.65 × V _{CC}	–	–	0.65 × V _{CC}	–	
			2.3 to 2.7	1.7	–	–	1.7	–	
			3.0 to 3.6	2.0	–	–	2.0	–	

NLV18SGxx, NLV28WGxx

Table 3. DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V _{CC} (V)	T _A = 25°C			T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
ALL OTHER FUNCTIONS									
V _{IL}	Low-Level Input Voltage		0.9	—	—	GND	—	GND	V
			1.1 to 1.3	—	—	0.3 x V _{CC}	—	0.3 x V _{CC}	
			1.4 to 1.6	—	—	0.35 x V _{CC}	—	0.35 x V _{CC}	
			1.65 to 1.95	—	—	0.35 x V _{CC}	—	0.35 x V _{CC}	
			2.3 to 2.7	—	—	0.7	—	0.7	
			3.0 to 3.6	—	—	0.8	—	0.8	
ALL FUNCTIONS									
V _{OH}	High-Level Output Voltage (Note 5)	V _{IN} = V _{IH} or V _{IL} I _{OH} = -20 µA I _{OH} = -0.3 mA I _{OH} = -1.7 mA I _{OH} = -3.0 mA I _{OH} = -4.0 mA I _{OH} = -8.0 mA	0.9 1.1 to 1.3 1.4 to 1.6 1.65 to 1.95 2.3 to 2.7 3.0 to 3.6	— 0.75 x V _{CC} 0.75 x V _{CC} V _{CC} - 0.45 2.0 2.48	0.75 — — — — —	— — — — — —	— 0.75 x V _{CC} 0.75 x V _{CC} V _{CC} - 0.45 2.0 2.48	— — — — — —	V
V _{OL}	Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 20 µA I _{OL} = 0.3 mA I _{OL} = 1.7 mA I _{OL} = 3.0 mA I _{OL} = 4.0 mA I _{OL} = 8.0 mA	0.9 1.1 to 1.3 1.4 to 1.6 1.65 to 1.95 2.3 to 2.7 2.7 to 3.6	— — — — — —	0.1 — — — 0.45 0.4	— 0.25 x V _{CC} 0.25 x V _{CC} 0.45 0.4	— — — — — —	— 0.25 x V _{CC} 0.25 x V _{CC} 0.45 0.4	V
I _{IN}	Input Leakage Current	V _{IN} = 3.6 V or GND	0.9 to 3.6	—	—	±0.1	—	±1.0	µA
I _{OZ}	3-State Output Leakage Current	V _{IN} = 0 V to 3.6 V; V _{OUT} = 0 V to 3.6 V	0.9 to 3.6	—	—	1.0	—	10.0	µA
I _{OFF}	Power Off Leakage Current (function U04 only)	V _{IN} = 0 V to 3.6 V	0	—	—	1.0	—	10.0	µA
	Power Off Leakage Current (except function U04)	V _{IN} = 0 V to 3.6 V; V _{OUT} = 0 V to 3.6 V	0	—	—	1.0	—	10.0	µA
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	3.6	—	—	1.0	—	10.0	µA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. The V_{OH} parameter does not apply to devices with open-drain output, NLV18SG06 and NLV18SG07.

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Table 4. AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Condition	V _{CC} (V)	T _A = 25°C			T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, (A or B) to Y (Figures 1 and 2)	C _L = 10 pF, R _L = 1 MΩ	0.9	—	27.3	—	—	—	ns
			1.1 to 1.3	—	13.0	22.6	—	35.9	
			1.4 to 1.6	—	7.5	10.5	—	11.3	
			1.65 to 1.95	—	6.0	7.8	—	8.2	
			2.3 to 2.7	—	4.3	5.4	—	5.8	
			3.0 to 3.6	—	3.5	4.4	—	4.6	
		C _L = 15 pF, R _L = 1 MΩ	0.9	—	29.5	—	—	—	
			1.1 to 1.3	—	14.3	25.1	—	41.6	
			1.4 to 1.6	—	8.0	11.5	—	12.6	
			1.65 to 1.95	—	6.3	8.4	—	8.7	
			2.3 to 2.7	—	4.6	5.7	—	6.1	
			3.0 to 3.6	—	3.7	4.6	—	5.0	
		C _L = 30 pF, R _L = 1 MΩ	0.9	—	40.5	—	—	—	
			1.1 to 1.3	—	19.6	35.7	—	58.1	
			1.4 to 1.6	—	10.7	15.8	—	17.6	
			1.65 to 1.95	—	7.8	10.7	—	11.7	
			2.3 to 2.7	—	5.4	6.9	—	8.1	
			3.0 to 3.6	—	4.3	5.2	—	6.1	
t _{PZH} , t _{PZL}	Output Enable Time, (A or OE) to Y (Figures 1 and 2)	C _L = 10 pF; R _L = 100 kΩ R _L = 5 kΩ	0.9	—	11.0	—	—	—	ns
			1.1 to 1.3	—	8.4	10.9	—	13.0	
			1.4 to 1.6	—	5.3	7.8	—	8.3	
			1.65 to 1.95	—	3.9	5.5	—	5.9	
			2.3 to 2.7	—	2.5	3.5	—	3.8	
			3.0 to 3.6	—	2.1	2.7	—	3.0	
			0.9	—	12.0	—	—	—	
		C _L = 15 pF; R _L = 100 kΩ R _L = 5 kΩ	1.1 to 1.3	—	9.0	11.7	—	13.8	
			1.4 to 1.6	—	5.9	8.9	—	11.0	
			1.65 to 1.95	—	4.4	6.3	—	6.5	
			2.3 to 2.7	—	2.9	3.9	—	4.2	
			3.0 to 3.6	—	2.3	3.0	—	3.3	
			0.9	—	13.0	—	—	—	
			1.1 to 1.3	—	10.0	13.1	—	15.2	
		C _L = 30 pF; R _L = 100 kΩ R _L = 5 kΩ R _L = 5 kΩ R _L = 5 kΩ	1.4 to 1.6	—	8.3	12.2	—	13.7	
			1.65 to 1.95	—	6.1	8.6	—	9.7	
			2.3 to 2.7	—	3.8	5.0	—	5.5	
			3.0 to 3.6	—	2.9	3.8	—	4.2	

NLV18SGxx, NLV28WGxx

Table 4. AC ELECTRICAL CHARACTERISTICS

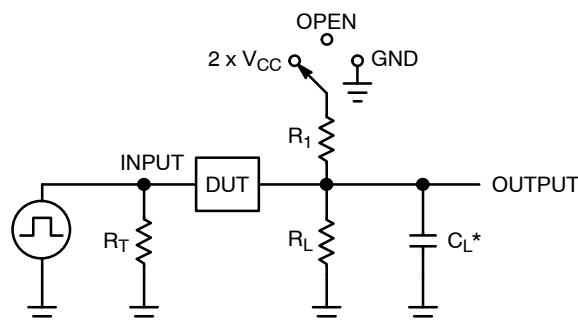
Symbol	Parameter	Test Condition	V _{CC} (V)	T _A = 25°C			T _A = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t _{PHZ} , t _{PLZ}	Output Disable Time, (A or OE) to Y (Figures 1 and 2)	C _L = 10 pF; R _L = 100 kΩ	0.9	—	100.4	—	—	—	ns
		R _L = 5 kΩ	1.1 to 1.3	—	9.1	14.4	—	22.4	
		R _L = 5 kΩ	1.4 to 1.6	—	7.1	9.1	—	10.4	
		R _L = 5 kΩ	1.65 to 1.95	—	6.5	8.3	—	9.0	
		R _L = 5 kΩ	2.3 to 2.7	—	5.8	7.3	—	8.8	
		R _L = 5 kΩ	3.0 to 3.6	—	5.4	6.9	—	7.6	
		C _L = 15 pF; R _L = 100 kΩ	0.9	—	122.2	—	—	—	
		R _L = 5 kΩ	1.1 to 1.3	—	9.8	15.3	—	25.1	
		R _L = 5 kΩ	1.4 to 1.6	—	7.8	9.8	—	11.3	
		R _L = 5 kΩ	1.65 to 1.95	—	7.2	9.2	—	10.6	
		R _L = 5 kΩ	2.3 to 2.7	—	7.0	8.2	—	10.3	
		R _L = 5 kΩ	3.0 to 3.6	—	6.6	7.7	—	9.5	
		C _L = 30 pF; R _L = 100 kΩ	0.9	—	217.1	—	—	—	
		R _L = 5 kΩ	1.1 to 1.3	—	13.2	19.6	—	31.9	
		R _L = 5 kΩ	1.4 to 1.6	—	12.2	13.5	—	14.9	
		R _L = 5 kΩ	1.65 to 1.95	—	11.4	12.7	—	13.9	
		R _L = 5 kΩ	2.3 to 2.7	—	11.3	12.2	—	13.5	
		R _L = 5 kΩ	3.0 to 3.6	—	10.2	11.5	—	12.9	

Table 5. CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V _{CC} = 3.6 V	3.0	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V _{CC} = 3.3 V, V _{IN} = 0 V or V _{CC}	4.0	pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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C_L includes probe and jig capacitance
 R_T is Z_{OUT} of pulse generator (typically 50 Ω)
 $f = 1$ MHz

Figure 1. Test Circuit

Test	Switch Position
t_{PLH} / t_{PHL}	Open
t_{PLZ} / t_{PZL}	$2 \times V_{CC}$
t_{PHZ} / t_{PZH}	GND

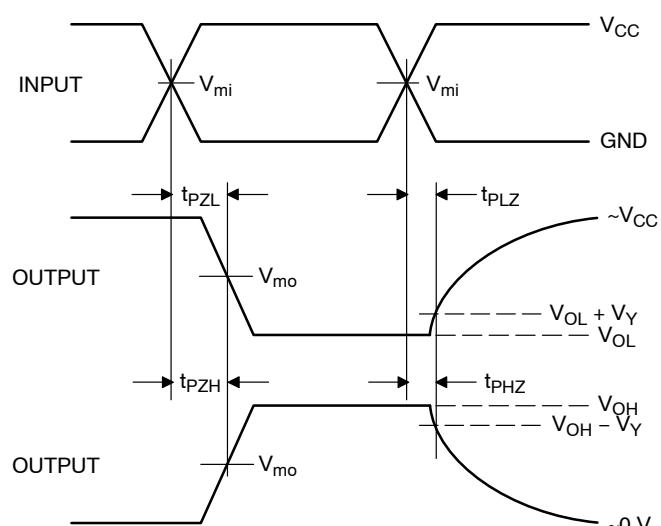
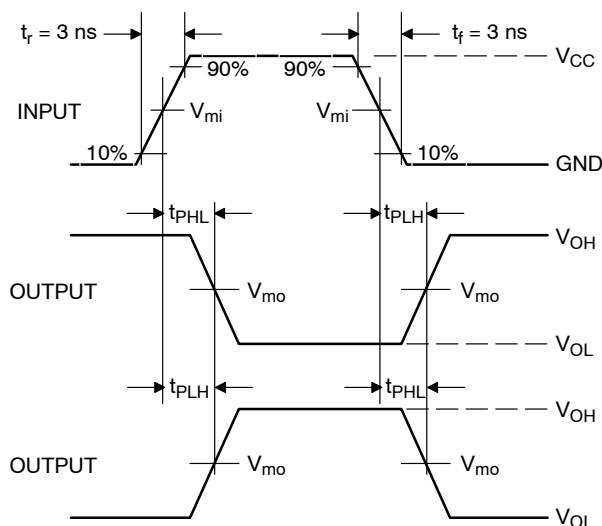


Figure 2. Switching Waveforms

V_{CC}, V	V_{mi}, V	V_{mo}, V	V_Y, V
0.9	$V_{CC}/2$	$V_{CC}/2$	0.1
1.1 to 1.3	$V_{CC}/2$	$V_{CC}/2$	0.1
1.4 to 1.6	$V_{CC}/2$	$V_{CC}/2$	0.1
1.65 to 1.95	$V_{CC}/2$	$V_{CC}/2$	0.15
2.3 to 2.7	$V_{CC}/2$	$V_{CC}/2$	0.15
3.0 to 3.6	1.5	1.5	0.3

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ORDERING INFORMATION

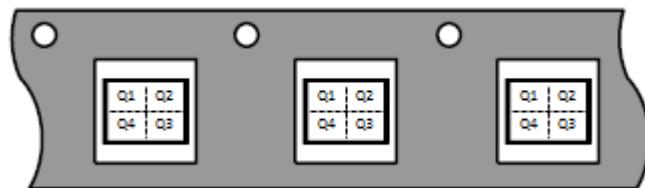
Device	Package	Marking	Pin 1 Orientation (See below)	Shipping [†]
NLV18SG08DFT2G	SC-88A	AT	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NVL Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

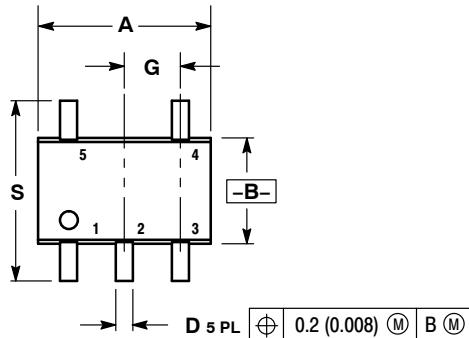
Pin 1 Orientation in Tape and Reel

Direction of Feed



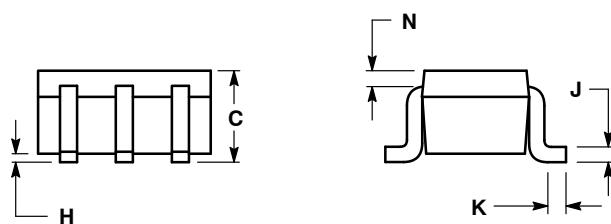
PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353)
CASE 419A-02
ISSUE L

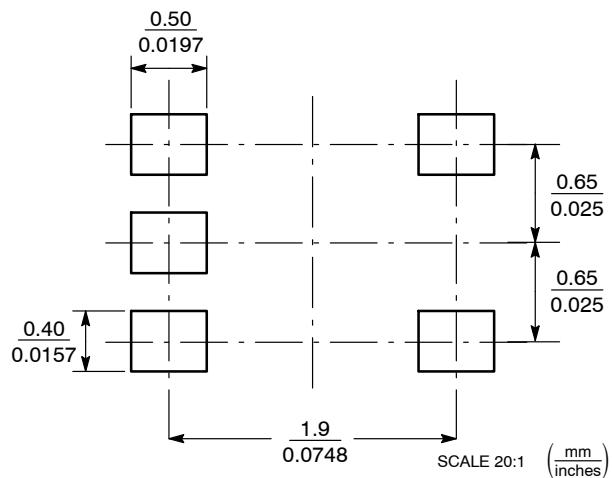


NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	0.026 BSC	0.65	0.65 BSC
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	0.008 REF	0.20	0.20 REF
S	0.079	0.087	2.00	2.20

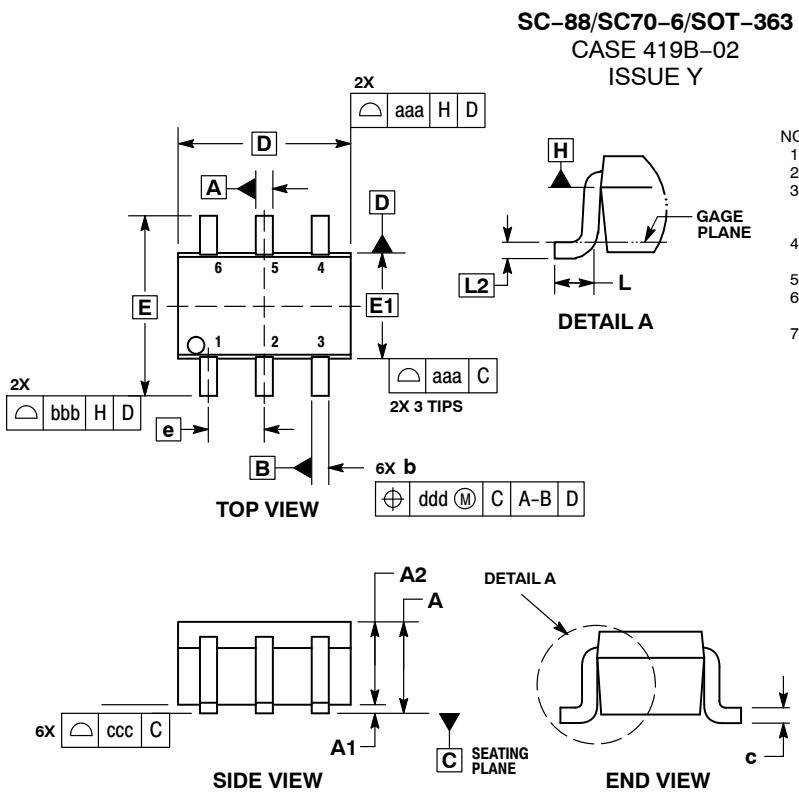


SOLDER FOOTPRINT



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PACKAGE DIMENSIONS

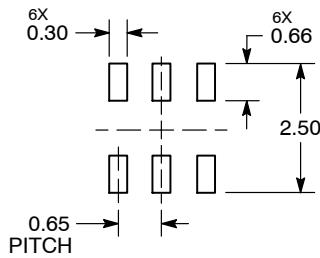


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.010	
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65	BSC			0.026	BSC
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15	BSC		0.006	BSC
aaa		0.15			0.006	
bbb		0.30			0.012	
ccc		0.10			0.004	
ddd		0.10			0.004	

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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